

# Zhuojun Chen

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/7387390/publications.pdf>

Version: 2024-02-01

24  
papers

271  
citations

1163117  
8  
h-index

940533  
16  
g-index

24  
all docs

24  
docs citations

24  
times ranked

511  
citing authors

#	ARTICLE	IF	CITATIONS
1	STT-MRAM-Based Reliable Weak PUF. IEEE Transactions on Computers, 2022, 71, 1564-1574.	3.4	6
2	A Physic-Based Explicit Compact Model for Reconfigurable Field-Effect Transistor. IEEE Access, 2021, 9, 46709-46716.	4.2	6
3	Analysis and Mitigation of Single-Event Gate Rupture in VDMOS With Termination Structure. IEEE Transactions on Nuclear Science, 2021, 68, 1272-1278.	2.0	4
4	Competitive Neural Network Circuit Based on Winner-Take-All Mechanism and Online Hebbian Learning Rule. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2021, 29, 1095-1107.	3.1	5
5	The Effect of Thermal Oxidation on the Photothermal Conversion Property of Tantalum Coatings. Materials, 2021, 14, 4031.	2.9	4
6	Design and Characterization of an SCR with separate bipolar transistors for ESD Protection. , 2021, , .		0
7	The Impact of Temperature on Reconfigurable Field-Effect Transistor and Its Applications. , 2021, , .		0
8	Impact of Radiation Effect on Ferroelectric Al-Doped HfO <sub>2</sub> Metal-Ferroelectric-Insulator-Semiconductor Structure. IEEE Access, 2020, 8, 108121-108126.	4.2	7
9	Design of a High-Performance Low-Cost Radiation-Hardened Phase-Locked Loop for Space Application. IEEE Transactions on Aerospace and Electronic Systems, 2020, 56, 3588-3598.	4.7	13
10	A Radiation-Hardened Dual-Direction SCR Based on LDMOS for ESD Protection in the Extreme Radiation Environment. IEEE Transactions on Nuclear Science, 2020, 67, 708-715.	2.0	6
11	The impact of radiation and temperature effects on dual-direction SCR devices for on-chip ESD protections. Semiconductor Science and Technology, 2020, 35, 045016.	2.0	3
12	Investigation of Total-Ionizing Dose Effects on the Two-Dimensional Transition Metal Dichalcogenide Field-Effect Transistors. IEEE Access, 2019, 7, 79989-79996.	4.2	7
13	Comparative Study of Total Ionizing Dose Effects on the Silicon-Controlled Rectifier Devices for HV and LV ESD Protections. , 2019, , .		0
14	A Comprehensive Study of a Bidirectional ESD Protection Device Under Harsh Environment. , 2019, , .		1
15	Tunable Schottky barrier width and enormously enhanced photoresponsivity in Sb doped SnS <sub>2</sub> monolayer. Nano Research, 2019, 12, 463-468.	10.4	71
16	High-performance asymmetric electrodes photodiode based on Sb/WSe <sub>2</sub> heterostructure. Nano Research, 2019, 12, 339-344.	10.4	32
17	Comparing the Gate Dependence of Contact Resistance and Channel Resistance in Organic Field-Effect Transistors for Understanding the Mobility Overestimation Issue. IEEE Electron Device Letters, 2018, 39, 421-423.	3.9	19
18	The Importance of Contact Resistance in High-Mobility Organic Field-Effect Transistors Studied by Scanning Kelvin Probe Microscopy. IEEE Electron Device Letters, 2018, 39, 276-279.	3.9	13

#	ARTICLE	IF	CITATIONS
19	Study of Total-Ionizing-Dose Effects on a Single-Event-Hardened Phase-Locked Loop. IEEE Transactions on Nuclear Science, 2018, 65, 997-1004.	2.0	8
20	Investigation of TID Effects on Subthreshold Bandgap Reference Circuits Fabricated in a SOI Process. , 2018, , .		1
21	Direct Observation of the Dipole-Induced Energetic Disorder in Rubrene Single-Crystal Transistors by Scanning Kelvin Probe Microscopy. Journal of Physical Chemistry Letters, 2018, 9, 2869-2873.	4.6	14
22	Correlation of Molecular Structure and Charge Transport Properties: A Case Study in Naphthalenediimide-Based Copolymer Semiconductors. Advanced Electronic Materials, 2018, 4, 1800203.	5.1	6
23	Analysis of Single-Event Effects in a Radiation-Hardened Low-Jitter PLL Under Heavy Ion and Pulsed Laser Irradiation. IEEE Transactions on Nuclear Science, 2017, 64, 106-112.	2.0	20
24	Single-Event Transient Characterization of a Radiation-Tolerant Charge-Pump Phase-Locked Loop Fabricated in 130 nm PD-SOI Technology. IEEE Transactions on Nuclear Science, 2016, 63, 2402-2408.	2.0	25